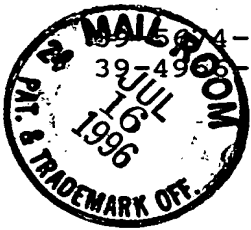


08/682009



39-4965-2SRD  
39-4965-2SRD DIV of

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :  
TOMOHARU TANAKA ET AL : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW APPLICATION :  
FILED: HEREWITH :  
FOR: NONVOLATILE SEMICONDUCTOR:  
MEMORY DEVICE

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend  
the above-identified application as follows:

IN THE SPECIFICATION

Page 3, line 10, change "restriction" to  
--restrictions--.

Page 5, line 16, after "cell" insert --,--;

line 17, after "written" insert --,--;

line 21, after "state" insert --at first--,  
same line, after "and" insert --is--.

Page 6, line 8, change "the" (first occurrence) to --a--.

Page 7, line 8, change "the" (first occurrence) to --a--.

Page 11, line 4, before "maximum" insert --a--.

Page 17, line 7, change "the" (first occurrence) to  
--a--.